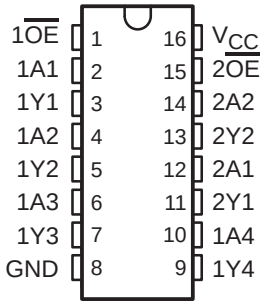
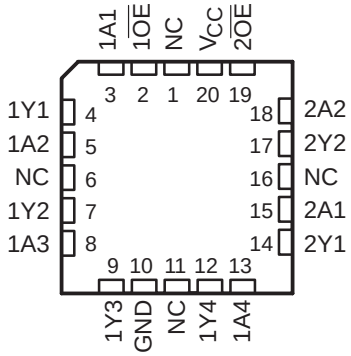
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Protection Exceeds JESD-22**
  - **2000-V Human-Body Model (A114-A)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**
- **Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages, Ceramic Flat (W) Packages, Chip Carriers (FK), and DIPs (J)**

SN54LV367A . . . J OR W PACKAGE
SN74LV367A . . . D, DB, DGV, NS, OR PW PACKAGE
(TOP VIEW)



SN54LV367A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

The ’LV367A devices are hex buffers and line drivers designed for 2-V to 5.5-V V_{CC} operation. These devices are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The ’LV367A devices are organized as dual 4-line and 2-line buffers/drivers with active-low output-enable ($1\overline{OE}$ and $2\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes noninverted data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

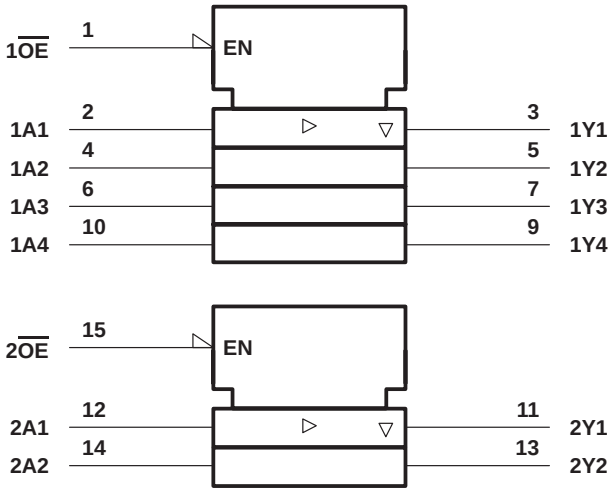
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54LV367A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV367A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer/driver)

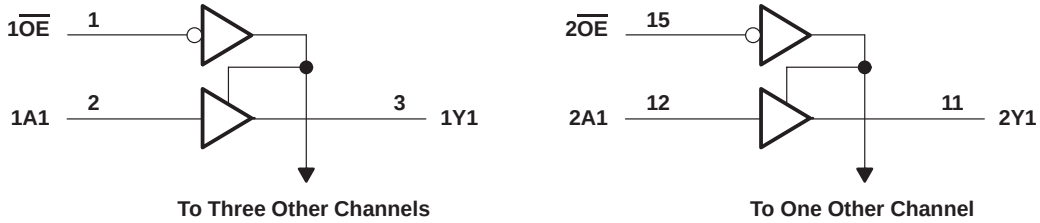
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, DGV, J, NS, PW, and W packages.

logic diagram (positive logic)



To Three Other Channels

To One Other Channel

Pin numbers shown are for the D, DB, DGV, J, NS, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Output voltage range applied in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range applied in high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±35 mA
Continuous current through V_{CC} or GND . . . . . ±70 mA
Package thermal impedance, θ_{JA} (see Note 3): D package . . . . . 73°C/W
DB package . . . . . 82°C/W
DGV package . . . . . 120°C/W
NS package . . . . . 64°C/W
PW package . . . . . 108°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 7 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			SN54LV367A		SN74LV367A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2	5.5	2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		1.5		V
		V_{CC} = 2.3 V to 2.7 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 3 V to 3.6 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
		V_{CC} = 4.5 V to 5.5 V	$V_{CC} \times 0.7$		$V_{CC} \times 0.7$		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5		0.5	V
		V_{CC} = 2.3 V to 2.7 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 3 V to 3.6 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
		V_{CC} = 4.5 V to 5.5 V		$V_{CC} \times 0.3$		$V_{CC} \times 0.3$	
V_I	Input voltage		0	5.5	0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	0	V_{CC}	V
		3-state	0	5.5	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2 V		–50		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2		–2	mA
		V_{CC} = 3 V to 3.6 V		–8		–8	
		V_{CC} = 4.5 V to 5.5 V		–16		–16	
I_{OL}	Low-level output current	V_{CC} = 2 V		50		50	μA
		V_{CC} = 2.3 V to 2.7 V		2		2	mA
		V_{CC} = 3 V to 3.6 V		8		8	
		V_{CC} = 4.5 V to 5.5 V		16		16	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V	0	200	0	200	ns/V
		V_{CC} = 3 V to 3.6 V	0	100	0	100	
		V_{CC} = 4.5 V to 5.5 V	0	20	0	20	
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LV367A			SN74LV367A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50 μA	2 V to 5.5 V	V_{CC}–0.1			V_{CC}–0.1			V
	I_{OH} = –2 mA	2.3 V	2			2			
	I_{OH} = –8 mA	3 V	2.48			2.48			
	I_{OH} = –16 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 50 μA	2 V to 5.5 V			0.1			0.1	V
	I_{OL} = 2 mA	2.3 V			0.4			0.4	
	I_{OL} = 8 mA	3 V			0.44			0.44	
	I_{OL} = 16 mA	4.5 V			0.55			0.55	
I_I	$V_I = V_{CC}$ or GND	5.5 V			±1			±1	μA
I_{OZ}	$V_O = V_{CC}$ or GND	5.5 V			±5			±5	μA
I_{CC}	$V_I = V_{CC}$ or GND, I_O = 0	5.5 V			20			20	μA
I_{off}	V_I or V_O = 0 to 5.5 V	0 V			5			5	μA
C_i	$V_I = V_{CC}$ or GND	3.3 V		3			3		pF
C_o	$V_I = V_{CC}$ or GND	3.3 V		5.2			5.2		pF

switching characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV367A		SN74LV367A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		6.4	12.7	1	16	1	16	ns
t_{en}*	$\overline{OE}$	Y			6.9	14.9	1	20	1	20	
t_{dis}*	$\overline{OE}$	Y			6.4	14.9	1	20	1	20	
t_{pd}	A	Y	C_L = 50 pF		8.6	17.5	1	21	1	21	ns
t_{en}	$\overline{OE}$	Y			9.4	19.7	1	25	1	25	
t_{dis}	$\overline{OE}$	Y			10.1	19.7	1	25	1	25	
$t_{sk(o)}$			C_L = 50 pF			2				2	ns

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV367A		SN74LV367A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		4.7	8.3	1	10	1	10	ns
t_{en}*	$\overline{OE}$	Y			5.1	10.5	1	12.5	1	12.5	
t_{dis}*	$\overline{OE}$	Y			4.9	10.5	1	12.5	1	12.5	
t_{pd}	A	Y	C_L = 50 pF		6.2	11.8	1	13.5	1	13.5	ns
t_{en}	$\overline{OE}$	Y			6.8	14	1	16	1	16	
t_{dis}	$\overline{OE}$	Y			7.3	13.6	1	15.5	1	15.5	
$t_{sk(o)}$			C_L = 50 pF			1.5				1.5	ns

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN54LV367A		SN74LV367A		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}*	A	Y	C_L = 15 pF		3.6	5.9	1	7	1	7	ns
t_{en}*	$\overline{OE}$	Y			3.8	7.2	1	8.5	1	8.5	
t_{dis}*	$\overline{OE}$	Y			2.6	7.2	1	8.5	0	8.5	
t_{pd}	A	Y	C_L = 50 pF		4.5	7.9	1	9	1	9	ns
t_{en}	$\overline{OE}$	Y			4.9	9.2	1	10.5	1	10.5	
t_{dis}	$\overline{OE}$	Y			4.5	9.2	1	10.5	0	10.5	
$t_{sk(o)}$			C_L = 50 pF			1				1	ns

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

noise characteristics, V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C (see Note 5)

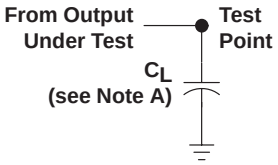
PARAMETER		SN74LV367A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.5	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		–0.2	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

NOTE 5: Characteristics are for surface-mount packages only.

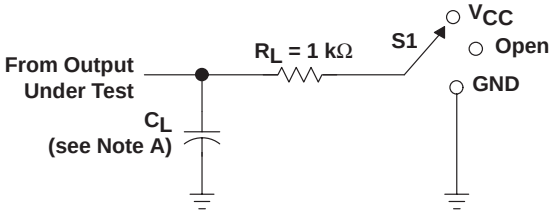
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	3.3 V	14.9	pF
			5 V	17.4	

PARAMETER MEASUREMENT INFORMATION

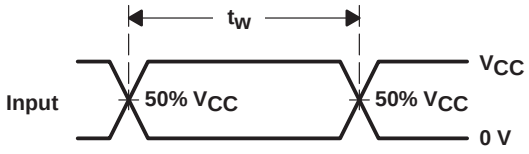


LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

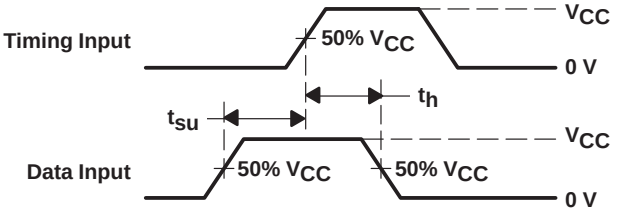


LOAD CIRCUIT FOR
3-STATE AND OPEN-DRAIN OUTPUTS

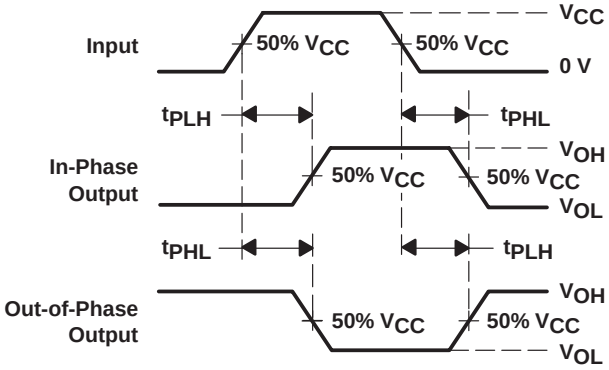
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}



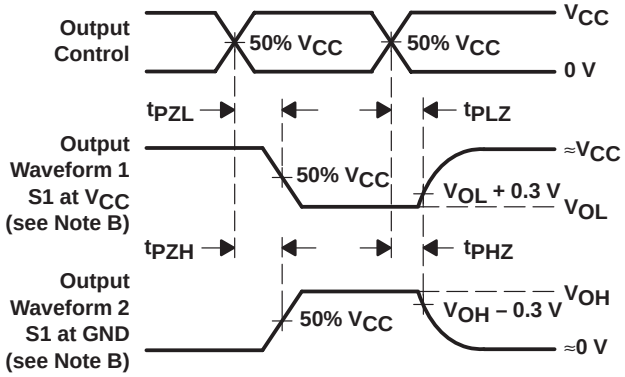
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
D. The outputs are measured one at a time with one input transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

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